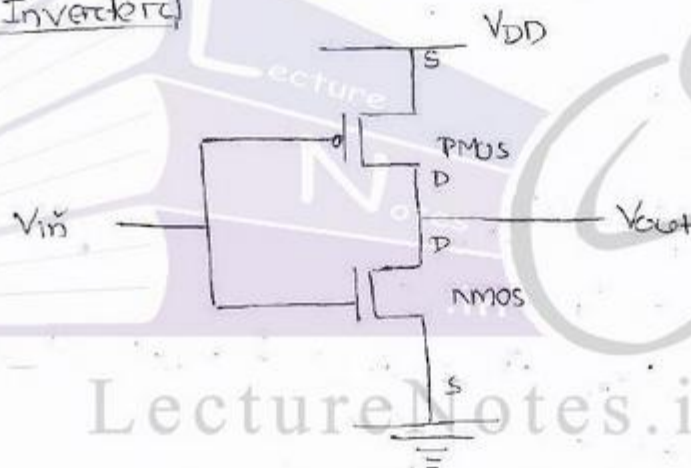


CMOS Inverter



Operating modes

for PMOS transistor,

$$V_{GS,P} = V_{G1} - V_{S1} \\ = V_{in} - V_{DD}$$

$$V_{DS,P} = V_{out} - V_{DD}$$

for NMOS transistor

$$V_{GS,n} = V_{G1} - V_{S1} \\ = V_{in} - 0 = V_{in}$$

$$V_{DS,n} = V_{out}$$

The NMOS transistor operates in linear region if

$$V_{DS,n} \leq V_{GS,n} - V_{T0,n}$$

$$V_{out} \leq V_{in} - V_{T0,n}$$

saturation region

$$V_{DS,n} \geq V_{GS,n} - V_{T0,n}$$

$$V_{out} \geq V_{in} - V_{T0,n}$$

Cutoff

$$V_{GS} < V_{T0,n}$$

$$V_{in} < V_{T0,n}$$

The PMOS transistor operates in linear region if

$$V_{DS,P} \geq V_{GS,P} - V_{T0,P}$$

$$V_{out} - V_{DD} \geq V_{in} - V_{DD} - V_{T0,P}$$

$$V_{out} \leq V_{in} - V_{th,P}$$

PMOS is in cut-off region if

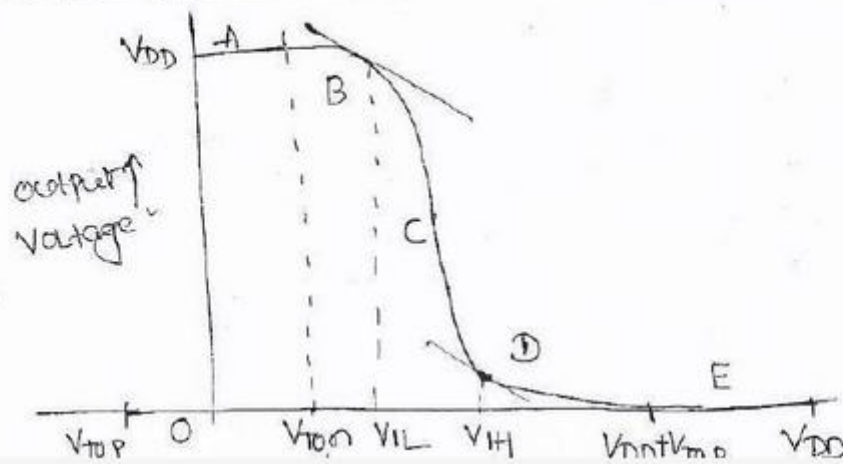
$$V_{GS,P} > V_{th,P}$$

$$V_{in} - V_{DD} > V_{th,P}$$

$$V_{in} > V_{DD} + V_{th,P}$$

VTC of CMOS inverter.

VTC of CMOS inverter.



Region	V_{in}	V_{out}	nMOS	pMOS
A	$< V_{thn}$	V_{OH}	cut-off	linear
B	V_{IL}	high V_{OH}	saturating	linear
C	V_{th}	V_{th}	saturating	saturating
D	V_{IH}	low V_{OL}	linear	saturating
E	$> V_{DD} + V_{thp}$	V_{OL}	linear	cut-off

In Region A, where $V_{in} < V_{thn}$ the nmos transistor is cutoff and the output voltage is equal to $V_{OH} = V_{DD}$. As the input voltage is increased beyond V_{thn} i.e. Region B, the nmos transistor starts conducting in saturation mode and the output voltage begins to decrease. The critical voltage V_{IL} corresponds to $dV_{out}/dV_{in} = -1$ located within Region B. As the output voltage further decreases, the pmos transistor enters saturation at Region C. The inverter threshold voltage, where $V_{in} = V_{out}$, is located in Region C. When the output voltage falls below $V_{in} - V_{thn}$, the nmos transistor starts to operate in linear mode. This corresponds to Region D where critical voltage point V_{IH} with $dV_{out}/dV_{in} = -1$ is located. Finally in Region E, with the input voltage $V_{in} > V_{DD} + V_{thp}$ the pmos transistor is cutoff and the output voltage is $V_{OL} = 0$.

Calculation of V_{IL}

$$V_{in} = V_{IL}$$

Slope of the VTC is equal to -1 i.e. $\frac{dV_{out}}{dV_{in}} = -1$
 nmos transistor operates in saturation
 and pmos transistor is in linear region.

$$I_{D,n} = I_{D,p}$$

$$\frac{K_n}{2} (V_{GS,n} - V_{TO,n})^2 = \frac{K_p}{2} [2(V_{GS,p} - V_{TO,p})V_{DS,p} - V_{DS,p}^2]$$

$$\frac{K_n}{2} (V_{in} - V_{TO,n})^2 = \frac{K_p}{2} [2(V_{in} - V_{DD} - V_{TO,p})(V_{out} - V_{DD}) - (V_{out} - V_{DD})^2]$$

Differentiating w.r.t. V_{in}

$$\frac{K_n}{2} [2(V_{in} - V_{TO,n})] = \frac{K_p}{2} [2(V_{in} - V_{DD} - V_{TO,p}) \frac{dV_{out}}{dV_{in}} + (V_{out} - V_{DD}) 2 \frac{dV_{out}}{dV_{in}} - 2(V_{out} - V_{DD}) \frac{dV_{out}}{dV_{in}}]$$

put $dV_{out}/dV_{in} = -1$

$$K_n [V_{in} - V_{TO,n}] = K_p [(V_{in} - V_{DD} - V_{TO,p})(-1) + (V_{out} - V_{DD})(-1) - (V_{out} - V_{DD})(-1)]$$

$$V_{in} = V_{IL}$$

$$K_n [V_{IL} - V_{TO,n}] = K_p [(V_{DD} + V_{TO,p} - V_{IL} + 2V_{out} - V_{DD} - V_{DD})]$$

$$K_n V_{IL} - K_n V_{TO,n} = K_p [V_{TO,p} - V_{IL} + 2V_{out} - V_{DD}]$$

$$\frac{K_n}{K_p} V_{IL} - \frac{K_n}{K_p} V_{TO,n} = V_{TO,p} + 2V_{out} - V_{DD} - V_{IL}$$

$$V_{IL} + \frac{K_n}{K_p} V_{IL} = V_{TO,p} + 2V_{out} - V_{DD} + \frac{K_n}{K_p} V_{TO,n}$$

$$V_{IL} [1 + K_R] = 2V_{out} + V_{TO,p} - V_{DD} + K_R V_{TO,n}$$

$$K_R = \frac{K_n}{K_p}$$

$$V_{IL} = \frac{2V_{out} + V_{TO,p} - V_{DD} + K_R V_{TO,n}}{1 + K_R}$$

2. calculation of V_{IH}

$$V_{in} = V_{IL}$$

nmos \rightarrow linear

pmos \rightarrow saturation

$$I_{D,P} = I_{D,n}$$

$$\frac{K_P}{2} [V_{GS,P} - V_{TO,P}]^2 = \frac{K_n}{2} [2(V_{GS,n} - V_{TO,n})V_{DS,n} - V_{DS,n}^2]$$

$$\frac{K_P}{2} [V_{in} - V_{DD} - V_{TO,P}]^2 = \frac{K_n}{2} [2(V_{in} - V_{TO,n})V_{out} - V_{out}^2]$$

differentiating w.r.t. V_{in}

$$\frac{K_P}{2} [2(V_{in} - V_{DD} - V_{TO,P})] = \frac{K_n}{2} [2(V_{in} - V_{TO,n}) \frac{dV_{out}}{dV_{in}} + 2V_{out} - 2V_{out} \frac{dV_{out}}{dV_{in}}]$$

$$\text{put } V_{in} = V_{IH}, \frac{dV_{out}}{dV_{in}} = -1$$

$$K_P(V_{IH} - V_{DD} - V_{TO,P}) = K_n[(V_{IH} - V_{TO,n})(-1) + V_{out} - V_{out}(-1)]$$

$$= K_n[V_{TO,n} - V_{IH} + 2V_{out}]$$

$$K_P V_{IH} - K_P V_{DD} - K_P V_{TO,P} = K_n V_{TO,n} - K_n V_{IH} + 2K_n V_{out}$$

$$(K_P + K_n) V_{IH} = K_P(V_{DD} + V_{TO,P}) + K_n(2V_{out} + V_{TO,n})$$

$$V_{IH} = \frac{K_P(V_{DD} + V_{TO,P}) + (2V_{out} + V_{TO,n})K_n}{K_P + K_n}$$

Dividing by k_n

$$V_{IH} = \frac{\frac{k_p}{k_n} (V_{DD} + V_{TO,P}) + 2V_{out} + V_{TO,n}}{1 + \frac{k_p}{k_n}}$$

$$= \frac{\frac{1}{K_R} (V_{DD} + V_{TO,P}) + 2V_{out} + V_{TO,n}}{1 + \frac{1}{K_R}}$$

$$V_{IH} = \frac{(V_{DD} + V_{TO,P}) + K_R(2V_{out} + V_{TO,n})}{1 + K_R}$$

3. calculation of V_{TH}

$$V_{in} = V_{TH}$$

pmos } saturation
nmos }

$$I_{D,P} = I_{D,n}$$

$$\frac{K_p}{2} (V_{GS,P} - V_{TO,P})^2 = \frac{K_n}{2} (V_{GS,n} - V_{TO,n})^2$$

$$K_p (V_{in} - V_{DD} - V_{TO,P})^2 = K_n (V_{in} - V_{TO,n})^2$$

$$K_p (V_{TH} - V_{DD} - V_{TO,P})^2 = K_n (V_{TH} - V_{TO,n})^2$$

$$(V_{DD} - V_{TH} + V_{TO,P})^2 = \frac{K_n}{K_p} (V_{TH} - V_{TO,n})^2$$

$$V_{DD} - V_{TH} + V_{TO,P} = \sqrt{\frac{K_n}{K_p}} (V_{TH} - V_{TO,n})$$

$$V_{DD} + V_{TO,P} - V_{TH} = \sqrt{K_R} (V_{TH} - V_{TO,n})$$

$$V_{DD} + V_{TO,P} + \sqrt{K_R} V_{TO,n} = \sqrt{K_R} V_{TH} + V_{TH}$$

$$V_{DD} + V_{TO,P} + \sqrt{K_R} V_{TO,n} = (\sqrt{K_R} + 1) V_{TH}$$

$$V_{TH} = \frac{V_{DD} + V_{TO,P} + \sqrt{K_R} V_{TO,n}}{1 + \sqrt{K_R}}$$

$$V_{TH} = \frac{V_{TO,n} + \frac{1}{\sqrt{K_R}} (V_{DD} + V_{TO,p})}{1 + \frac{1}{\sqrt{K_R}}}$$

Design of CMOS Inverters

The inverter threshold voltage is one of the most important parameters of the CMOS inverter circuit.

$$V_{TH} + \frac{1}{\sqrt{K_R}} V_{TH} = V_{TO,n} + \frac{1}{\sqrt{K_R}} (V_{DD} + V_{TO,p})$$

$$V_{TH} - V_{TO,n} = \frac{1}{\sqrt{K_R}} (V_{DD} + V_{TO,p} - V_{TH})$$

$$\frac{1}{\sqrt{K_R}} = \frac{V_{TH} - V_{TO,n}}{V_{DD} + V_{TO,p} - V_{TH}}$$

For an ideal CMOS inverter $V_{TH} = \frac{V_{DD}}{2}$ ✓

$$\left(\frac{K_n}{K_p}\right)_{ideal} = \left[\frac{V_{DD} + V_{TO,p} - \frac{V_{DD}}{2}}{\frac{V_{DD}}{2} - V_{TO,n}} \right]^2$$

$$= \left[\frac{0.5 V_{DD} - V_{TO,p}}{0.5 V_{DD} - V_{TO,n}} \right]^2$$

For symmetric inverter

$$V_{TO,n} = V_{TO,p}$$

$$\left(\frac{k_n}{k_p}\right)_{\text{symmetric inverter}} = 1$$

The ratio k_R is defined as

$$\frac{k_n}{k_p} = \frac{\mu_n C_{ox} \left(\frac{W}{L}\right)_n}{\mu_p C_{ox} \left(\frac{W}{L}\right)_p}$$

$$k_R = \frac{\mu_n \left(\frac{W}{L}\right)_n}{\mu_p \left(\frac{W}{L}\right)_p}$$

assuming that the gate oxide thickness t_{ox} and hence, the gate oxide capacitance C_{ox} have the same value for both nMOS and pMOS transistors

$$\frac{\left(\frac{W}{L}\right)_n \mu_n}{\left(\frac{W}{L}\right)_p \mu_p} = 1 \quad \text{symmetric inverter}$$

$$\frac{\left(\frac{W}{L}\right)_n}{\left(\frac{W}{L}\right)_p} = \frac{\mu_p}{\mu_n} \approx \frac{230 \text{ cm}^2/\text{V}\cdot\text{s}}{580 \text{ cm}^2/\text{V}\cdot\text{s}}$$

$$\boxed{\left(\frac{W}{L}\right)_p \approx 2.5 \left(\frac{W}{L}\right)_n}$$

Symmetric CMOS inverter

$$V_{TO,n} = -|V_{TO,p}|$$

$$k_R = 1$$

$$V_{IL} = \frac{2V_{DD} + V_{TO,p} - V_{DD} + k_R V_{TO,n}}{1 + k_R} \quad \hat{A}$$

$$\frac{2V_{DD} + 2V_{T0,n} - V_{DD}}{2}$$

pmos \rightarrow linear
nmos \rightarrow saturation

$$V_{IL} = \frac{1}{8} (3V_{DD} + 2V_{T0,n})$$

$$V_{IH} = \frac{1}{8} (5V_{DD} - 2V_{T0,n})$$

in a symmetric inverter the sum of V_{IL} & V_{IH} is always equal to V_{DD}

$$V_{IL} + V_{IH} = V_{DD}$$

Noise margin

$$NM_L = V_{IL} - V_{OL} = V_{IL}$$

$$NM_H = V_{OH} - V_{IH} = V_{DD} - V_{IH}$$

Symmetric inverter

$$V_{OH} = V_{DD}$$

$$V_{OL} = 0$$

Q consider a CMOS inverter circuit with the following parameters:

$$V_{DD} = 3.3V$$

$$V_{T0,n} = 0.6V$$

$$V_{T0,p} = -0.7V$$

$$K_n = 200 \mu A/V^2$$

$$K_p = 80 \mu A/V^2$$

calculate the noise margins of the circuit. Notice that the CMOS inverter being considered here has $K_R = 2.5$ and $V_{T0,n} \neq |V_{T0,p}|$ hence it is not a symmetric inverter.

$$\underline{V_{IL}} \quad V_{IL} = \frac{2V_{DD} + V_{TP} - V_{DD} + K_R V_{TN}}{1 + K_R}$$

$$= \frac{2V_{DD} - 0.7 - 3.3 + 2.5 \times 0.6}{1 + 2.5}$$

$$\boxed{V_{IL} = 0.57V_{DD} - 0.71}$$

PMOS \rightarrow linear
NMOS \rightarrow saturation

$$\frac{K_n}{2} (V_{in} - V_{TN})^2 = \frac{K_p}{2} [2(V_{in} - V_{DD} - V_{TP})(V_{DD} - V_{in}) - (V_{DD} - V_{in})^2]$$

$$2.5(0.57V_{DD} - 0.71 - 0.6)^2 = 2(0.57V_{DD} - 0.71 - 3.3 + 0.7)(V_{DD} - 3.3) - (V_{DD} - 3.3)^2$$

$$0.66V_{DD}^2 + 0.05V_{DD} - 6.65 = 0$$

$$\boxed{V_{DD} = 3.14V} \quad \because V_{DD} > 0$$

$$V_{IL} = 0.57V_{DD} - 0.71$$

$$= 0.57 \times 3.14 - 0.71$$

$$\boxed{V_{IL} = 1.08V}$$

$$\underline{V_{IH}} \quad V_{IH} = \frac{V_{DD} + V_{TP} + K_R(2V_{DD} + V_{TN})}{1 + K_R}$$

$$= \frac{3.3 - 0.7 + 2.5(2V_{DD} + 0.6)}{1 + 2.5}$$

$$V_{IH} = 1.43V_{DD} + 1.17$$

PMOS \rightarrow saturation

NMOS \rightarrow linear

$$\frac{k_n}{2} [2(V_{in} - V_{Tn}) \cdot V_{out} - V_{out}^2] = \frac{k_p}{2} (V_{in} - V_{DD} - V_{Tp})^2$$

$$2.5 [2(1.43V_{out} + 1.17 - 0.6)V_{out} - V_{out}^2] = (1.43V_{out} + 1.17 - 3.3 + 0.7)^2$$

$$2.61V_{out}^2 + 6.94V_{out} - 2.04 = 0$$

$$V_{out} = 0.27V$$

$$V_{IH} = 1.43V_{out} + 1.17$$

$$= 1.43 \times 0.27 + 1.17$$

$$V_{IH} = 1.55V$$

Noise margin

$$NM_L = V_{IL} - V_{OL} = 1.08V \quad \because V_{OL} = 0$$

$$NM_H = V_{OH} - V_{IH} = 3.3 - 1.55 = 1.75V \quad \because V_{OH} = V_{DD}$$

Advantages of CMOS inverter

i) Static power dissipation is Zero.

ii) Noise margin is high.

iii) Provides full output voltage swing between 0V & V_{DD} .

Disadvantages of CMOS inverter

i) It occupies more area.

ii) Circuit complexity is more.